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There is a typo of the space group. All the Pnmb should be Pbnm (or Pnma). So the Glazer notation should be changed to (a/a’ c’) for Pbnm space group on page 4 of the article.¹ We have also noticed that the thermodynamic analysis of CaTiO₃ thin film is not correct. The films are (001)PC-oriented or (101)-oriented. Therefore, there is no need to rotate the coordinate system (on page 4 of the article¹). By applying the thin film boundary condition, i.e., \( \varepsilon_{11} = \varepsilon_{22} = \varepsilon_{33} = 0 \), and minimizing the total free energy with respect to epitaxial strain, \( \varepsilon_{s} \), a temperature-strain phase diagram is determined. All the strain and stress components should be in the original coordinate system. The corrected phase diagrams are shown in the figures below. For LSAT phase diagrams (Figs. 5(a) and 5(b)), the ferroelectric transition is better described using the Fmm2 phase because the calculated phase boundary is much closer to the experimental value than using the Aba2 phase. The NGO phase diagram, as shown in Fig. 5(c), is essentially the same as Gu’s orthorhombic Pbnm CaTiO₃ film calculation,² which is also (001)PC-oriented. All the other analysis and conclusions in the article¹ are not affected. We apologize to the readers for the confusion that might have been caused. The authors would like to thank Ryan Haislmaier for pointing out the mistake.


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FIG. 5. The calculated temperature-strain phase diagram for CaTiO₃ films grown on (a) and (b) LSAT and (c) NGO substrates. The corresponding measured experimental transition temperatures are indicated on the phase diagrams. \( P_1 \) and \( P_2 \) are in-plane polarization component and \( P_3 \) is out-of-plane component. The polarization component not shown for a specific phase is zero.

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